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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Complete if Known	
				Application Number	10/036,156-Conf. #3974
				Filing Date	December 26, 2001
				First Named Inventor	Dae Gyu Park
				Art Unit	2813
				Examiner Name	Jack S.J. Chen
Sheet	1	of	1	Attorney Docket Number	29936/37830

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
		JP-6-5852	01-14-1994	Oki Electric Ind. Co. Ltd.	English Abstract Only	
		JP-9-143699	06-03-1997	Nissin Electric Co. Ltd.	English Abstract Only	
		JP-11-172438	06-29-1999	Samsung Electron Co. Ltd.	English Abstract Only	
		JP-2000-54134	02-22-2000	Samsung Electronics Co. Ltd.	English Abstract Only	
		JP-2000-91269	03-31-2000	Fujitsu Ltd.	English Abstract Only	
		JP-2000-124154	04-28-2000	Sony Corp.	English Abstract Only	

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		Official Action issued from Japanese Patent Office dated May 25, 2005	

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U.S. Department of Commerce
Patent and Trademark OfficeApp. Docket No.
29936/37830Serial No.
(to be assigned)

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Applicant

Dae Gyu PARK

Filing Date
(herewith-12/26/01)Group 2813
Unknown

U.S. PATENT DOCUMENTS

*Examiner Initials	Document Number	Issue Date	Name	Class	Subclass	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS

*Examiner Initials	Document Number	Publication Date	Country	Class	Subclass	Translation	
						Yes	No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

~	C1	Park, Dae-Gyu, et al., "Properties of reactive-sputtered $Ti_{1-x}Al_xN$ thin films", Meeting Abstracts of The 195 th Meeting of The Electrochemical Society, Inc. in Seattle, Washington on May 2-6, 1999, Abstract No. 476
~	C2	Moriwaki, M., et al., "Impacts of Chlorine in CVD-TiN Gate Electrode on the Gate Oxide Reliability in Multiple-Thickness Oxide Technology", Extended Abstracts of the 2000 International Conference on Solid State Devices and Materials, Sendai, 2000, pp. 188-189
~	C3	Hu, J.C., et al., "Feasibility of Using W/TiN as Metal Gate for Conventional 0.13 μm CMOS Technology and Beyond", International Electron Devices Meeting (IEDM 97) pp. 825-828, ©1997 IEEE
~	C4	Nakajima, K., et al., "Work Function Controller Metal Gate Electrode on Ultrathin Gate Insulators", 1999 Symposium on VLSI Technology Digest of Technical Papers, pp. 95-96
~	C5	Amazawa, T., et al., "Surface State Generation of Mo Gate Metal Oxide Semiconductor Devices Caused by Mo Penetration into Gate Oxide", J. Electrochem. Soc., Vol. 145, No. 4, April 1998, © The Electrochemical Society, Inc.

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